

N-Channel JFET

Low-Frequency Low-Noise Amplifier

BSR58

Description

This device is designed for low-power chopper or switching application sourced from process 51.

ABSOLUTE MAXIMUM RATINGS

($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DGO}	Drain–Gate Voltage	40	V
V_{GSO}	Gate–Source Voltage	–40	V
I_{GF}	Forward Gate Current	50	mA
P_{tot}	Total Power Dissipation Up to $T_{amb} = 40^\circ\text{C}$		

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